



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

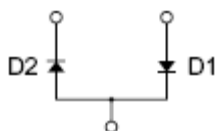
SOT-523 Plastic-Encapsulate Diode

DA221 SWITCHING DIODE

FEATURES:

- Bias circuits
- Protection circuits

MARKING: K



SOT-523



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25 °C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	20	V
DC reverse voltage	V _R	20	V
Maximum (peak) forward current	I _{FM}	200	mA
Average forward current	I _O	100	mA
Power dissipation	P _D	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 100μA	20		V
Reverse voltage leakage current	I _R	V _R =15V		0.1	μA
Forward voltage	V _F	I _F =10mA		1	V

Typical Characteristics

DA221

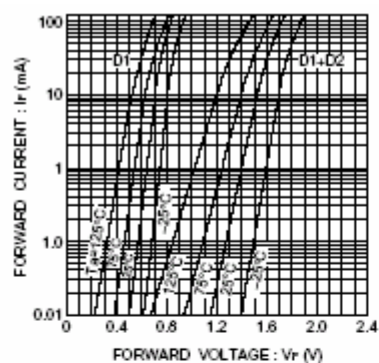


Fig.1 Forward characteristics

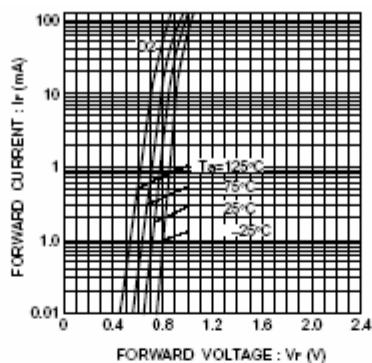


Fig.2 Forward characteristics

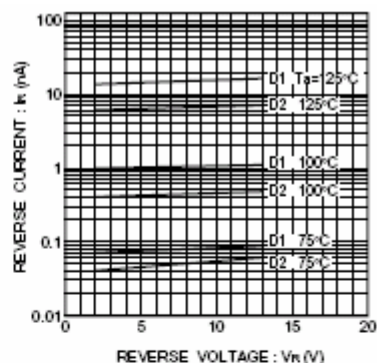


Fig.3 Reverse characteristics

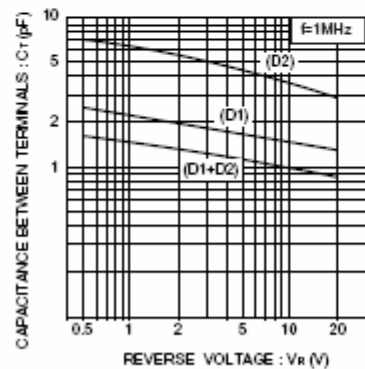


Fig.4 Capacitance between terminals characteristics